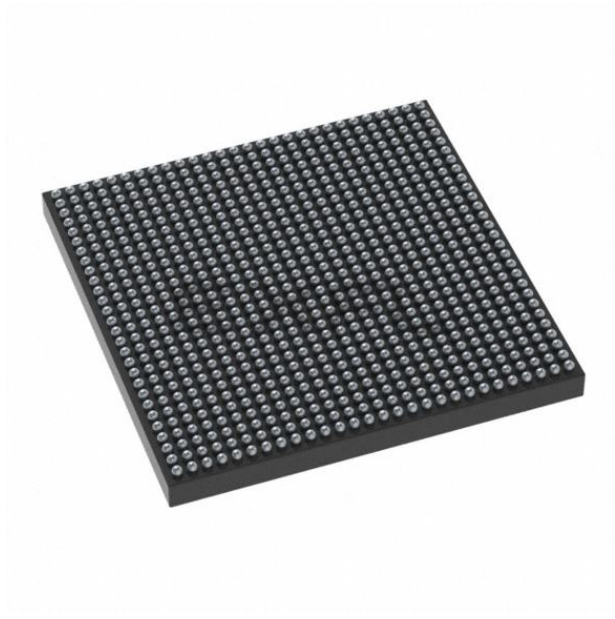

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 103K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	784-BFBGA, FCBGA
Supplier Device Package	784-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu2cg-1sfvc784i

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	–0.500	1.650	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	–0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	–0.500	3.630	V
V_{PSIN}[2]	PS I/O input voltage.	–0.500	V_{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	–0.500	V_{CCO_PSDDR} + 0.550	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	–0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}[3]	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	–0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}[4]	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}[2][5][7]	I/O input voltage for HD I/O banks.[6]	–0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	–0.550	V_{CCO} + 0.550	V
I_{DC}	Available output current at the pad.	–20	20	mA
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.[8]	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.[9]	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.[10]	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(12)	–	260	°C
T_j	Maximum junction temperature.(12)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 6: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	100%	–0.40	78%
V_{CCO} + 0.45	100%	–0.45	40%
V_{CCO} + 0.50	100%	–0.50	24%
V_{CCO} + 0.55	100%	–0.55	18.0%
V_{CCO} + 0.60	100%	–0.60	13.0%
V_{CCO} + 0.65	100%	–0.65	10.8%
V_{CCO} + 0.70	92%	–0.70	9.0%
V_{CCO} + 0.75	92%	–0.75	7.0%
V_{CCO} + 0.80	92%	–0.80	6.0%
V_{CCO} + 0.85	92%	–0.85	5.0%
V_{CCO} + 0.90	92%	–0.90	4.0%
V_{CCO} + 0.95	92%	–0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 7: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	100%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Power Supply Sequencing

PS Power-On/Off Power Supply Sequencing

The low-power domain (LPD) must operate before the full-power domain (FPD) can function. The low-power and full-power domains can be powered simultaneously. The PS_POR_B input must be asserted to GND during the power-on sequence (see Table 37). The FPD (when used) must be powered before PS_POR_B is released.

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the low-power domain (LPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTLP}$
2. V_{CC_PSAUX}, V_{CC_PSADC}, and V_{CC_PSPLL} in any order or simultaneously.
3. V_{CCO_PSIO}

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the full-power domain (FPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTFP}$ and $V_{CC\_PSINTFP\_DDR}$ driven from the same supply source.
2. $V_{PS\_MGTRAVCC}$ and $V_{CC\_PSDDR\_PLL}$ in any order or simultaneously.
3. $V_{PS\_MGTRAVTT}$ and V_{CCO_PSDDR} in any order or simultaneously.

PL Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}/V_{CCINT_VCU}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTH or GTY transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HD I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 23: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{CCO}(1)	Supply voltage.	2.375	2.500	2.625	V
V_{IDIFF}	Differential input voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	100	350	600(2)	mV
V_{ICM}	Input common-mode voltage.	0.300	1.200	1.425	V

Notes:

1. LVDS_25 in HD I/O banks supports inputs only. LVDS_25 inputs without internal termination have no V_{CCO} requirements. Any V_{CCO} can be chosen as long as the input voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 24: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}(1)	Supply voltage.		1.710	1.800	1.890	V
V_{ODIFF}(2)	Differential output voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	454	mV
V_{OCM}(2)	Output common-mode voltage.	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}(3)	Differential input voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600(3)	mV
V_{ICM_DC}(4)	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
V_{ICM_AC}(5)	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In HP I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for LVDS_PRE_EMPHASIS = FALSE.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. EQUALIZATION = EQ_NONE (Default).
5. External input common mode voltage specification for AC coupled configurations. EQUALIZATION = EQ_LEVEL0, EQ_LEVEL1, EQ_LEVEL2, EQ_LEVEL3, EQ_LEVEL4.

Table 37: **PS Reset Assertion Timing Requirements**

Symbol	Description	Min	Typ	Max	Units
T_{PSPOR}	Required PS_POR_B assertion time.(1)	10	–	–	µs
T_{PSRST}	Required PS_SRST_B assertion time.	3	–	–	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: **PS Clocks Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{TOPSW\_MAINMAX}$	TOPSW_MAIN maximum frequency.	600	533	533	MHz
$F_{TOPSW\_LSBUSMAX}$	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
$F_{GDMAMAX}$	FPD-DMA maximum frequency.	600	600	600	MHz
$F_{DPDMAMAX}$	DisplayPort DMA maximum frequency.	600	600	600	MHz
$F_{LPD\_SWITCH\_CTRLMAX}$	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
$F_{LPD\_LSBUS\_CTRLMAX}$	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
$F_{ADMAMAX}$	LPD-DMA maximum frequency.	600	500	500	MHz
$F_{APLL\_TO\_LPDMAX}$	APLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{DPLL\_TO\_LPDMAX}$	DPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{VPLL\_TO\_LPDMAX}$	VPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{IOPLL\_TO\_LPDMAX}$	IOPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{RPLL\_TO\_FPDMAX}$	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

Programmable Logic (PL) Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Zynq UltraScale+ MPSoC. These values are subject to the same guidelines as the AC Switching Characteristics, page 22. In each table, the I/O bank type is either high performance (HP) or high density (HD).

Table 70: **LVDS Component Mode Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)(1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX DDR	HD	0	250	0	250	0	250	0	250	0	250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)(1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX SDR	HD	0	125	0	125	0	125	0	125	0	125	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 71: **LVDS Native Mode Performance(1)(2)**

Description	DATA_WIDTH	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3(3)		-2(3)		-1		-2(3)		-1		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s
LVDS RX DDR (RX_BITSLICE)(4)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS RX SDR (RX_BITSLICE)(4)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s

Notes:

1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite. The performance values assume a source-synchronous interface.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is PLL_F_{VCOMIN}/2.
3. In the SBVA484 package, the maximum data rate is 1260 Mb/s for DDR interfaces and 630 Mb/s for SDR interfaces.
4. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces *(Cont'd)***

Memory Standard	Package(1)	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages and FBVB900	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
	SFVC784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
QDR II+	All	Single rank component(7)	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages and FBVB900	Single rank component	1200	1200	1066	1066	933	MHz
	SFVC784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:

1. The SBVA484 and SFVA625 packages do not support the PL memory interfaces.
2. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
3. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
4. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
5. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
6. Includes: 2 rank 2 slot, 4 rank 1 slot.
7. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_F	0.856	0.856	0.900	0.856	0.900	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
HSTL_I_S	0.856	0.856	0.900	0.856	0.900	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
HSUL_12_F	0.780	0.780	0.867	0.780	0.867	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
HSUL_12_S	0.780	0.780	0.867	0.780	0.867	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
LVCMOS12_F_12	0.918	0.918	0.976	0.918	0.976	1.689	1.689	1.856	1.689	1.856	1.202	1.202	1.317	1.202	1.317	ns
LVCMOS12_F_4	0.918	0.918	0.976	0.918	0.976	1.742	1.742	1.922	1.742	1.922	1.353	1.353	1.478	1.353	1.478	ns
LVCMOS12_F_8	0.918	0.918	0.976	0.918	0.976	1.714	1.714	1.879	1.714	1.879	1.292	1.292	1.432	1.292	1.432	ns
LVCMOS12_S_12	0.918	0.918	0.976	0.918	0.976	2.073	2.073	2.247	2.073	2.247	1.581	1.581	1.717	1.581	1.717	ns
LVCMOS12_S_4	0.918	0.918	0.976	0.918	0.976	1.979	1.979	2.182	1.979	2.182	1.633	1.633	1.772	1.633	1.772	ns
LVCMOS12_S_8	0.918	0.918	0.976	0.918	0.976	2.205	2.205	2.406	2.205	2.406	1.767	1.767	1.928	1.767	1.928	ns
LVCMOS15_F_12	0.905	0.905	0.958	0.905	0.958	1.713	1.713	1.892	1.713	1.892	1.275	1.275	1.428	1.275	1.428	ns
LVCMOS15_F_16	0.905	0.905	0.958	0.905	0.958	1.722	1.722	1.881	1.722	1.881	1.260	1.260	1.407	1.260	1.407	ns
LVCMOS15_F_4	0.905	0.905	0.958	0.905	0.958	1.825	1.825	1.959	1.825	1.959	1.453	1.453	1.557	1.453	1.557	ns
LVCMOS15_F_8	0.905	0.905	0.958	0.905	0.958	1.778	1.778	1.930	1.778	1.930	1.378	1.378	1.458	1.378	1.458	ns
LVCMOS15_S_12	0.905	0.905	0.958	0.905	0.958	1.991	1.991	2.139	1.991	2.139	1.516	1.516	1.648	1.516	1.648	ns
LVCMOS15_S_16	0.905	0.905	0.958	0.905	0.958	2.172	2.172	2.389	2.172	2.389	1.707	1.707	1.888	1.707	1.888	ns
LVCMOS15_S_4	0.905	0.905	0.958	0.905	0.958	2.313	2.313	2.483	2.313	2.483	1.952	1.952	2.123	1.952	2.123	ns
LVCMOS15_S_8	0.905	0.905	0.958	0.905	0.958	2.170	2.170	2.400	2.170	2.400	1.817	1.817	1.984	1.817	1.984	ns
LVCMOS18_F_12	0.915	0.915	0.958	0.915	0.958	1.805	1.805	1.962	1.805	1.962	1.383	1.383	1.471	1.383	1.471	ns
LVCMOS18_F_16	0.915	0.915	0.958	0.915	0.958	1.785	1.785	1.917	1.785	1.917	1.338	1.338	1.446	1.338	1.446	ns
LVCMOS18_F_4	0.915	0.915	0.958	0.915	0.958	1.868	1.868	2.013	1.868	2.013	1.472	1.472	1.599	1.472	1.599	ns
LVCMOS18_F_8	0.915	0.915	0.958	0.915	0.958	1.797	1.797	1.979	1.797	1.979	1.384	1.384	1.487	1.384	1.487	ns
LVCMOS18_S_12	0.915	0.915	0.958	0.915	0.958	2.201	2.201	2.408	2.201	2.408	1.762	1.762	1.894	1.762	1.894	ns
LVCMOS18_S_16	0.915	0.915	0.958	0.915	0.958	2.173	2.173	2.362	2.173	2.362	1.702	1.702	1.834	1.702	1.834	ns
LVCMOS18_S_4	0.915	0.915	0.958	0.915	0.958	2.346	2.346	2.567	2.346	2.567	1.951	1.951	2.092	1.951	2.092	ns
LVCMOS18_S_8	0.915	0.915	0.958	0.915	0.958	2.292	2.292	2.511	2.292	2.511	1.848	1.848	2.008	1.848	2.008	ns
LVCMOS25_F_12	0.988	0.988	1.042	0.988	1.042	2.153	2.153	2.453	2.153	2.453	1.692	1.692	1.856	1.692	1.856	ns
LVCMOS25_F_16	0.988	0.988	1.042	0.988	1.042	2.105	2.105	2.406	2.105	2.406	1.623	1.623	1.786	1.623	1.786	ns
LVCMOS25_F_4	0.988	0.988	1.042	0.988	1.042	2.344	2.344	2.554	2.344	2.554	1.842	1.842	2.039	1.842	2.039	ns
LVCMOS25_F_8	0.988	0.988	1.042	0.988	1.042	2.184	2.184	2.516	2.184	2.516	1.726	1.726	1.910	1.726	1.910	ns
LVCMOS25_S_12	0.988	0.988	1.042	0.988	1.042	2.558	2.558	2.840	2.558	2.840	1.971	1.971	2.194	1.971	2.194	ns
LVCMOS25_S_16	0.988	0.988	1.042	0.988	1.042	2.449	2.449	2.740	2.449	2.740	1.852	1.852	2.063	1.852	2.063	ns
LVCMOS25_S_4	0.988	0.988	1.042	0.988	1.042	2.770	2.770	3.066	2.770	3.066	2.224	2.224	2.458	2.224	2.458	ns
LVCMOS25_S_8	0.988	0.988	1.042	0.988	1.042	2.663	2.663	2.963	2.663	2.963	2.091	2.091	2.373	2.091	2.373	ns
LVCMOS33_F_12	1.154	1.154	1.213	1.154	1.213	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVCMOS33_F_16	1.154	1.154	1.213	1.154	1.213	2.383	2.383	2.603	2.383	2.603	1.734	1.734	1.869	1.734	1.869	ns
LVCMOS33_F_4	1.154	1.154	1.213	1.154	1.213	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVCMOS33_F_8	1.154	1.154	1.213	1.154	1.213	2.603	2.603	2.822	2.603	2.822	1.937	1.937	2.130	1.937	2.130	ns
LVCMOS33_S_12	1.154	1.154	1.213	1.154	1.213	2.705	2.705	3.047	2.705	3.047	2.049	2.049	2.318	2.049	2.318	ns
LVCMOS33_S_16	1.154	1.154	1.213	1.154	1.213	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVCMOS33_S_4	1.154	1.154	1.213	1.154	1.213	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns

Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

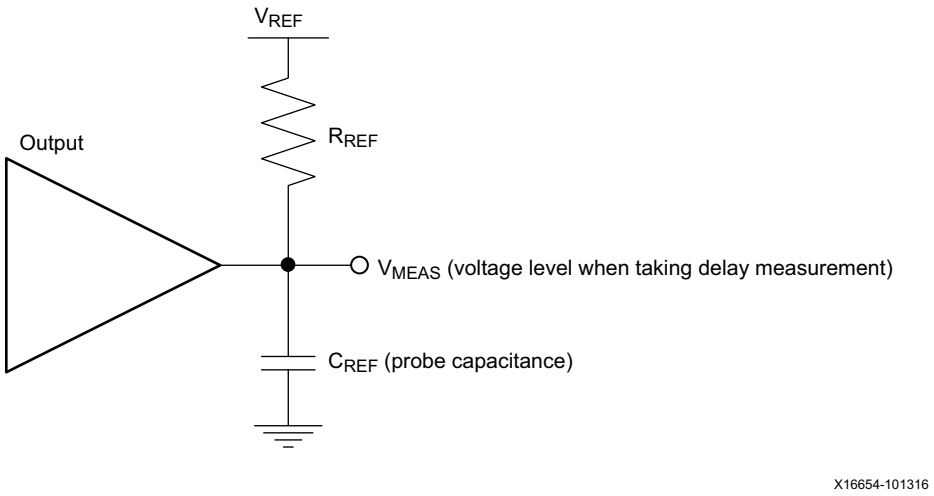

Figure 1: **Single-Ended Test Setup**

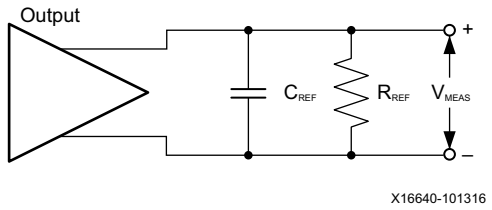

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 79.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

UltraRAM Switching Characteristics

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoC that include this memory.

Table 81: **UltraRAM Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F_{MAX}	UltraRAM maximum frequency with OREG_B = True.	650	600	575	500	481	MHz
F_{MAX_ECC}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = True.	450	400	386	325	315	MHz
$F_{MAX\_NORPIPELINE}$	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = False.	550	500	478	425	408	MHz
T_{PW} (1)	Minimum pulse width.	650	700	730	800	832	ps
T_{RSTPW}	Asynchronous reset minimum pulse width. One cycle required.	1 clock cycle					

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Input/Output Delay Switching Characteristics

Table 82: **Input/Output Delay Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{REFCLK}	REFCLK frequency for IDELAYCTRL (component mode).	300 to 800					MHz
	REFCLK frequency for BITSLICE_CONTROL (native mode). (1)	300 to 2666.67	300 to 2666.67	300 to 2400	300 to 2400	300 to 2133	MHz
T_{MINPER_CLK}	Minimum period for IODELAY clock.	3.195	3.195	3.195	3.195	3.195	ns
T_{MINPER_RST}	Minimum reset pulse width.	52.00					ns
$T_{IDELAY\_RESOLUTION}$/ $T_{ODELAY\_RESOLUTION}$	IDELAY/ODELAY chain resolution.	2.1 to 12					ps

Notes:

1. PLL settings could restrict the minimum allowable data rate. For example, when using a PLL with CLKOUTPHY_MODE = VCO_HALF, the minimum frequency is PLL_FVCOMIN/2.

MMCM Switching Characteristics

Table 85: **MMCM Specification**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{INMAX}$	Maximum input clock frequency.	1066	933	800	933	800	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency.	10	10	10	10	10	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max					
$MMCM\_F_{INDUTY}$	Input duty cycle range: 10–49 MHz.	25–75					%
	Input duty cycle range: 50–199 MHz.	30–70					%
	Input duty cycle range: 200–399 MHz.	35–65					%
	Input duty cycle range: 400–499 MHz.	40–60					%
	Input duty cycle range: >500 MHz.	45–55					%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase shift clock frequency.	0.01	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase shift clock frequency.	550	500	450	500	450	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency.	800	800	800	800	800	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency.	1600	1600	1600	1600	1600	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical.(1)	1.00	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.(1)	4.00	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.(2)	0.12	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter.	Note 3					
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty cycle precision.(4)	0.165	0.20	0.20	0.20	0.20	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time for $MMCM\_F_{PFDMIN}$.	100	100	100	100	100	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency.	891	775	667	725	667	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency.(4)(5)	6.25	6.25	6.25	6.25	6.25	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max					
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector.	550	500	450	500	450	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector.	10	10	10	10	10	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path.	5 ns Max or one clock cycle					

Table 88: **Global Clock Input to Output Delay Without MMCM (Far Clock Region)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF_FAR}	Global clock input and output flip-flop *without* MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: **Global Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
$T_{ICKOFMMCMCC}$	Global clock input and output flip-flop *with* MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
		XCZU19	2.44	2.44	2.66	3.19	3.17	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

GTH Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further information.

Table 97: **GTH Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F_{GTHMAX}	GTH maximum line rate.		16.375(1)		16.375(1)		12.5		12.5		10.3125		Gb/s
F_{GTHMIN}	GTH minimum line rate.		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHCRANGE}$	CPLL line rate range(2).	1	4	12.5	4	12.5	4	8.5	4	8.5	4	8.5	Gb/s
		2	2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	Gb/s
		4	1	3.125	1	3.125	1	2.125	1	2.125	1	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.0625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHQRANGE1}$	QPLL0 line rate range(3).	1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	12.5	9.8	10.3125	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.15	4.9	8.1875	4.9	8.15	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.075	2.45	4.0938	2.45	4.075	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0375	1.225	2.0469	1.225	2.0375	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0188	0.6125	1.0234	0.6125	1.0188	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHQRANGE2}$	QPLL1 line rate range(4).	1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	12.5	8.0	10.3125	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{CPLLRANGE}$	CPLL frequency range.		2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	GHz
$F_{QPLL0RANGE}$	QPLL0 frequency range.		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
$F_{QPLL1RANGE}$	QPLL1 frequency range.		8	13	8	13	8	13	8	13	8	13	GHz

Notes:

1. GTH transceiver line rates in the SFVC784 package support data rates up to 12.5 Gb/s.
2. The values listed are the rounded results of the calculated equation (2 x CPLL_Frequency)/Output_Divider.
3. The values listed are the rounded results of the calculated equation (QPLL0_Frequency)/Output_Divider.
4. The values listed are the rounded results of the calculated equation (QPLL1_Frequency)/Output_Divider.

Table 98: **GTH Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	All Speed Grades	Units
$F_{GTHDRPCLK}$	GTHDRPCLK maximum frequency.	250	MHz

Table 99: **GTH Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 100: **GTH Transceiver Reference Clock Oscillator Selection Phase Noise Mask**

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$[(1)(2)]	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
$CPLL_{REFCLKMASK}$[(1)(2)]	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
		50 MHz	–	–	–140	

Notes:

1. For reference clock frequencies other than 312.5 MHz, adjust the phase-noise mask values by 20 x Log(N/312.5) where N is the new reference clock frequency in MHz.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Table 101: **GTH Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock.		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37×10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3×10^6	UI

Table 102: **GTH Transceiver User Clock Switching Characteristics[(1)]**

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3[(2)]	-2[(2)(3)]	-1[(4)(5)]	-2[(3)]	-1[(5)]	
$F_{TXOUTPMA}$	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz
$F_{RXOUTPMA}$	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz

Table 103: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHTX}	Serial data rate range		0.500	–	F_{GTHMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.0}$	Total jitter(3)(4)	4.0 Gb/s	–	–	0.32	UI
$D_{J4.0}$	Deterministic jitter(3)(4)		–	–	0.16	UI
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI

GTY Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include the GTY transceivers.

GTY Transceiver DC Input and Output Levels

Table 106 and Table 107 summarize the DC specifications of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 106: **GTY Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based)	When remote RX is terminated to GND	$V_{MGTAVTT}/2 - D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX\_TERM}}{2}\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled	Equation based	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance		–	100	–	Ω
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the GTY transceiver attributes discussed in the *UltraScale Architecture GTY Transceiver User Guide* (UG578) and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

PL SYSMON I2C/PMBus Interfaces

Table 125: **PL SYSMON I2C Fast Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	µs
T_{SMFCKH}	SCL High time	0.6	–	µs
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:
1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: **PL SYSMON I2C Standard Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	µs
T_{SMSCKH}	SCL High time	4.0	–	µs
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:
1. The test conditions are configured to the LVCMOS 1.8V I/O standard.